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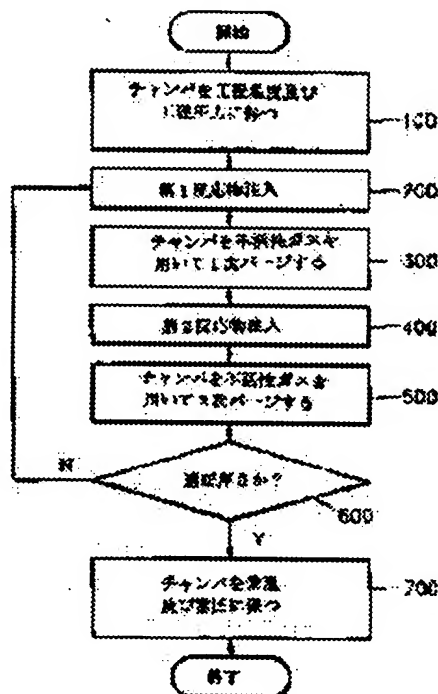
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(54) PRODUCTION OF THIN FILM

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a thin film producing method by an atomic layer vapor deposition method.

SOLUTION: This method comprises a stage 100 in which the temp. and pressure in a chamber loaded with a substrate are held to prescribed ones, a stage 200 in which a primary reactant is poured into the chamber and is chemically adsorbed on the substrate, a stage 300 in which the chamber contg. the substrate in which chemically adsorbed primary reactant has been formed is primarily purged with an inert gas, and the physically adsorbed primary reactant is left on the chemically adsorbed primary reactant, a stage 400 in which a secondary reactant is poured into the chamber contg. the substrate in which the chemically adsorbed and physically adsorbed primary reactant has been formed and is reacted therewith to form a thin film and a stage 500 in which the chamber in which the thin film has been formed is secondarily purged with an inert gas.



LEGAL STATUS

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